

9/208,105

048Woa-1

18

Abstract of Disclosure

An object of the present invention is to provide a semiconductor device capable of radiating electron-beams only to a desired region without forming a layer for restricting the radiating rays. A source electrode 22 made of aluminum prevents the generation of bremsstrahlung even when the electron-beams are radiated to the source electrode in a exposed condition. Also, the source electrode having an opening 25 at above of a crystal defect region 11 is used as a mask when the electron-beams are radiated thereto. That is the source electrode made of aluminum can be used both as a wiring and a mask for the radiating rays.

SECRET

"Express Mail" mailing label number EL176165550US

Date of Deposit November 25, 1998

I hereby certify that this paper or file is being deposited with the United States Patent Office for the purpose of Mail Post Office is "Patent Office" service under 37 C.F.R. 1.10 on the date indicated above and is acknowledged by the Commissioner of Patents and Trademarks, Washington, D.C. 20231

D. McCruder
DMC
8/12/1998